Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Material: Metal **Overall Length:** Between 0.300 inches and 0.400 inches **Overall Diameter:** 0.424 inches **Mounting Facility Quantity:** 1 **Internal Configuration:** Junction contact Electrode Internally-electrically Connected To Case: Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.424 inches and 0.437 inches

Thread Size:

0.190 inches

Criticality Code Justification:

Feat

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

2.0 gate trigger voltage, dc and 1.8 on-state voltage, dc

Current Rating Per Characteristic:

7.00 amperes forward current, total rms nanoamperes and 30.00 milliamperes forward current, total rms preset

Special Features:

Item must comply w/rqmt of desc production standard no. L00881; junction pattern arrangement: pnpn

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 threaded stud and 2 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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